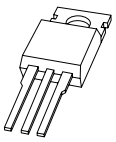


PHP79NQ08LT

N-channel TrenchMOS logic level FET

Rev. 01 — 21 July 2005 Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology.

1.2 Features

- Very low on-state resistance
- Logic level compatible

1.3 Applications

- Motors, lamps and solenoids
- Uninterruptible power supplies
- DC-to-DC converters
- General purpose power switching

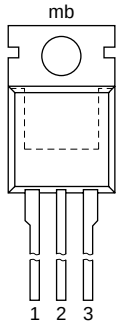
1.4 Quick reference data

- $E_{DS(AL)S} \leq 120$ mJ
- $I_D \leq 73$ A
- $P_{tot} \leq 157$ W
- $R_{DSon} \leq 16$ mΩ

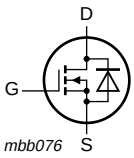
2. Pinning information

Table 1: Pinning

Pin	Description	Simplified outline	Symbol
1	gate (G)		
2	drain (D)		
3	source (S)		
mb	mounting base; connected to drain		



SOT78 (TO-220AB)



PHILIPS

3. Ordering information

Table 2: Ordering information

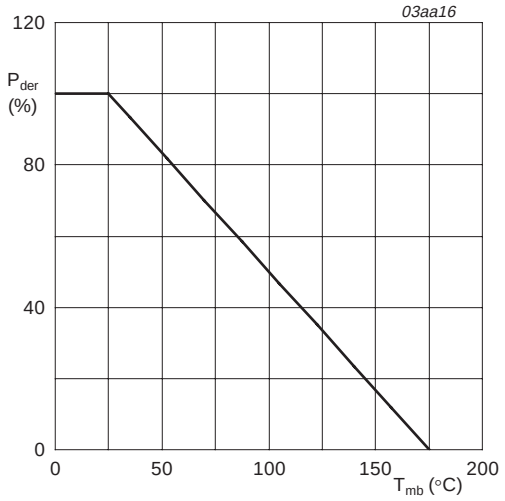
Type number	Package		
	Name	Description	Version
PHP79NQ08LT	SC-46	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 3: Limiting values

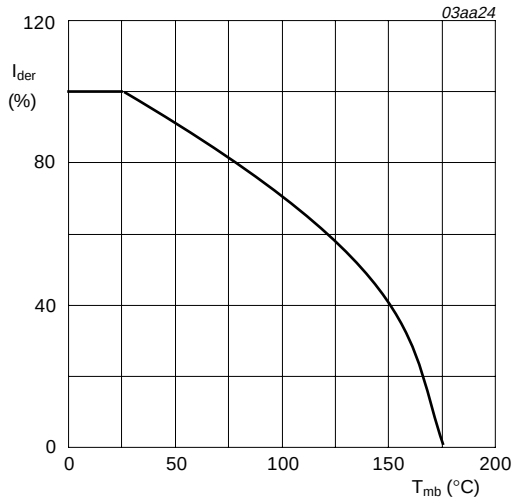
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C	-	75	V
V_{DGR}	drain-gate voltage (DC)	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	75	V
V_{GS}	gate-source voltage		-	±15	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 5 V; Figure 2 and 3	-	67	A
		T_{mb} = 100 °C; V_{GS} = 5 V; Figure 2	-	47	A
		T_{mb} = 25 °C; V_{GS} = 10 V	-	73	A
		T_{mb} = 100 °C; V_{GS} = 10 V	-	51	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; t_p ≤ 10 µs; Figure 3	-	240	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Figure 1	-	157	W
T_{stg}	storage temperature		–55	+175	°C
T_j	junction temperature		–55	+175	°C
Source-drain diode					
I_{DR}	reverse drain current	T_{mb} = 25 °C	-	67	A
I_{DRM}	peak reverse drain current	T_{mb} = 25 °C; pulsed; t_p ≤ 10 µs	-	270	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; I_D = 35 A; t_p = 0.07 ms; V_{DD} ≤ 75 V; R_{GS} = 50 Ω; V_{GS} = 10 V; starting at T_j = 25 °C	-	120	mJ



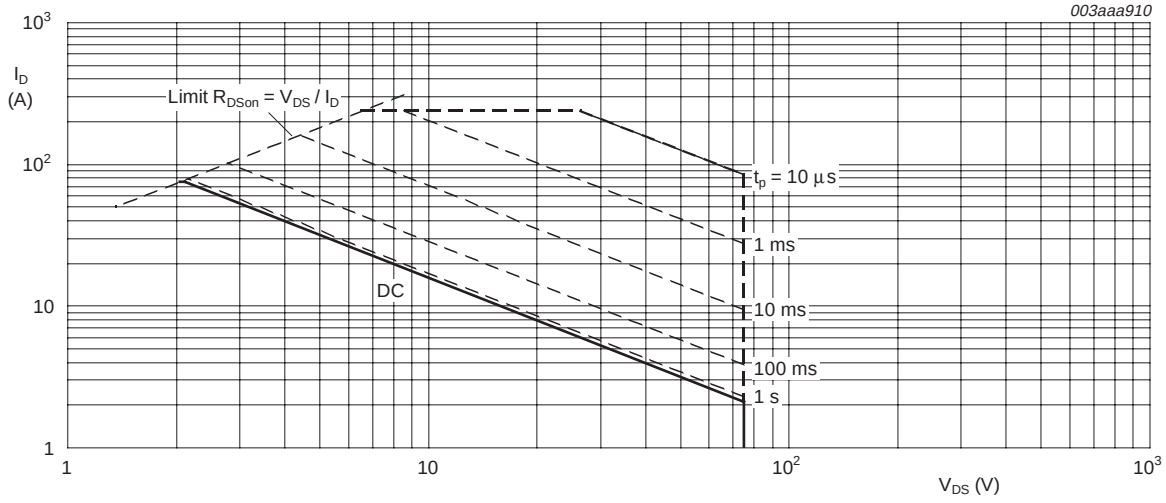
$$P_{der} = \frac{P_{tot}}{P_{tot(25\ ^\circ C)}} \times 100\ \%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25\ ^\circ C)}} \times 100\ \%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

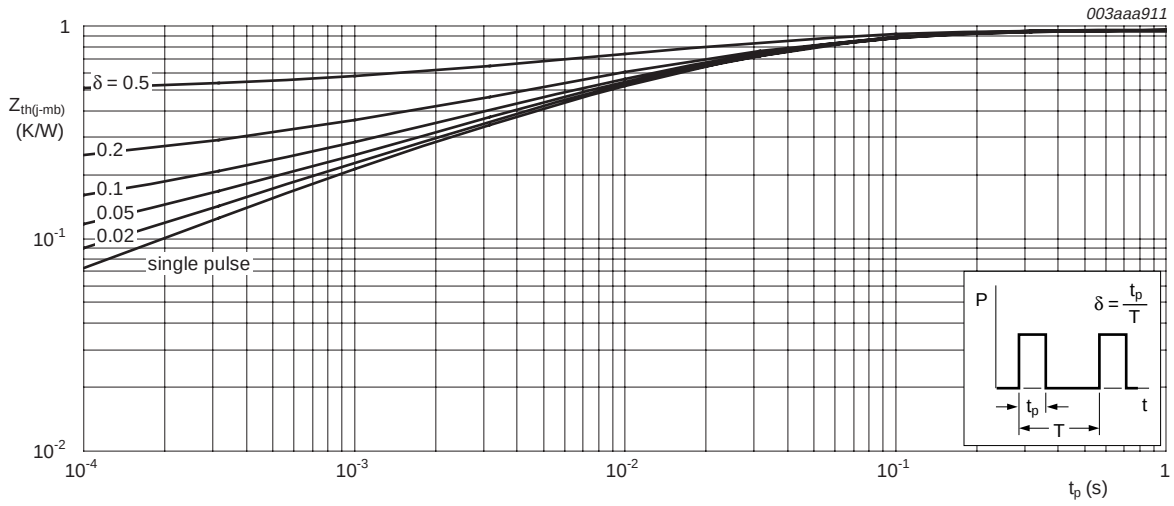


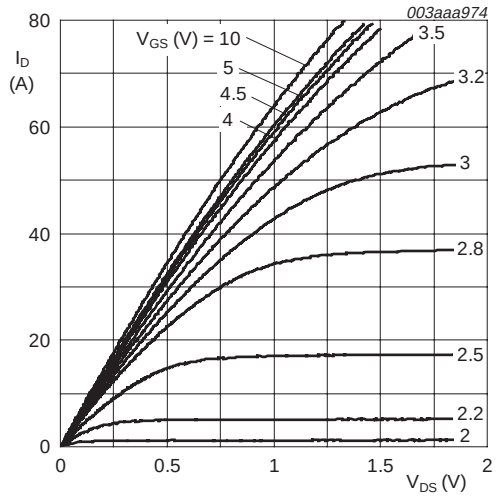
Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 5: Characteristics

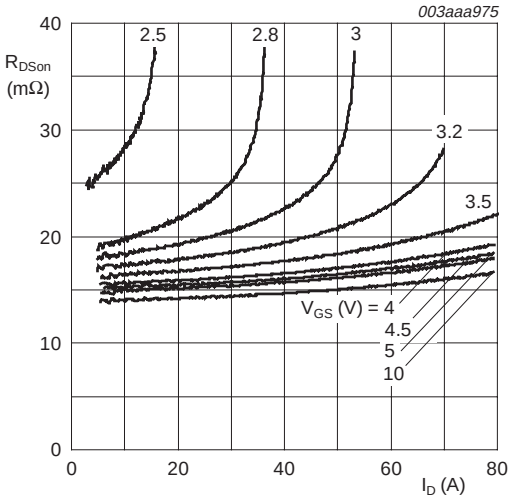
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V				
		T_j = 25 °C	75	-	-	V
		T_j = –55 °C	70	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; Figure 9 and 10				
		T_j = 25 °C	1.1	1.5	2	V
		T_j = 175 °C	0.5	-	-	V
		T_j = –55 °C	-	-	2.3	V
I_{DSS}	drain leakage current	V_{DS} = 75 V; V_{GS} = 0 V				
		T_j = 25 °C	-	0.02	1	µA
		T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = ±15 V; V_{DS} = 0 V	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 25 A; Figure 6 and 8				
		T_j = 25 °C	-	15	16.4	mΩ
		T_j = 175 °C	-	-	34	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; Figure 6 and 8	-	15.5	18	mΩ
		V_{GS} = 10 V; I_D = 25 A; Figure 6 and 8	-	14	16	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DD} = 60 V; V_{GS} = 5 V; Figure 11 and 12	-	30	-	nC
Q_{GS}	gate-source charge		-	6	-	nC
Q_{GD}	gate-drain charge		-	14	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; Figure 14	-	3 026	-	pF
C_{oss}	output capacitance		-	301	-	pF
C_{rss}	reverse transfer capacitance		-	140	-	pF
$t_{d(on)}$	turn-on delay time	V_{DD} = 30 V; R_L = 1.2 Ω; V_{GS} = 5 V; R_G = 10 Ω	-	30	-	ns
t_r	rise time		-	102	-	ns
$t_{d(off)}$	turn-off delay time		-	101	-	ns
t_f	fall time		-	57	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; Figure 13	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = –100 A/µs; V_{GS} = –10 V; V_{DS} = 30 V	-	90	-	ns
Q_r	recovered charge		-	110	-	nC



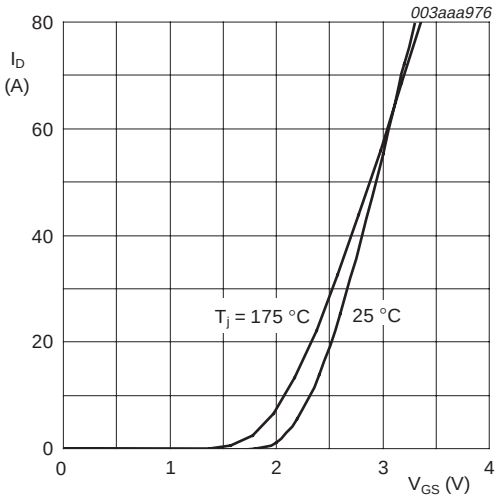
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



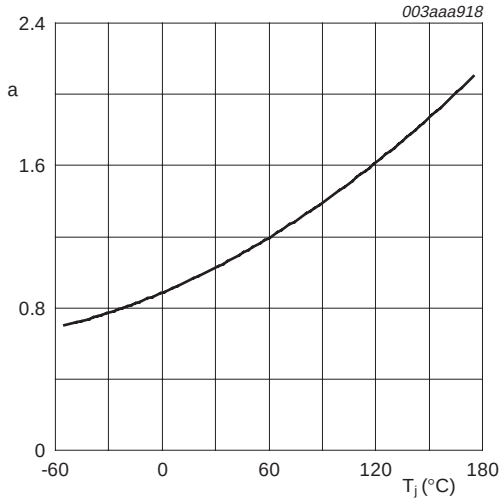
T_j = 25 °C

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



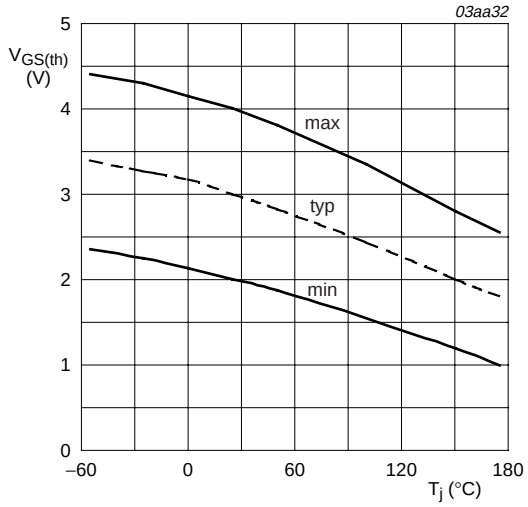
T_j = 25 °C and 175 °C; $V_{DS} > I_D \times R_{DSon}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



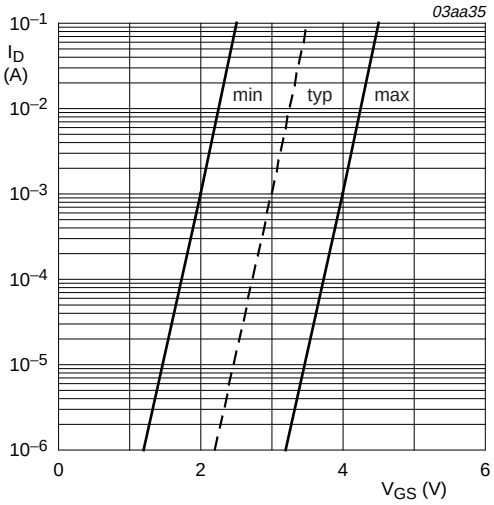
$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



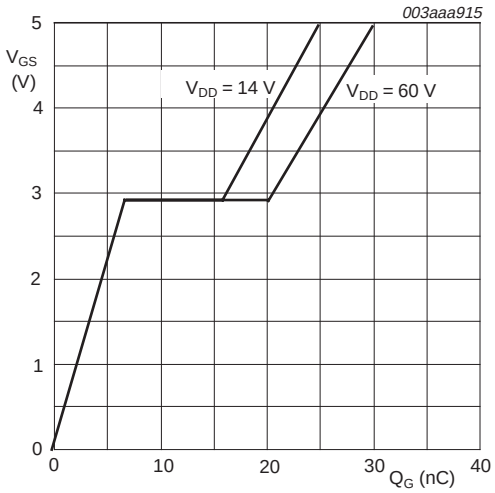
I_D = 1 mA; V_{DS} = V_{GS}

Fig 9. Gate-source threshold voltage as a function of junction temperature



T_j = 25 °C; V_{DS} = 5 V

Fig 10. Sub-threshold drain current as a function of gate-source voltage



I_D = 25 A; V_{DS} = 14 V and 60 V

Fig 11. Gate-source voltage as a function of gate charge; typical values

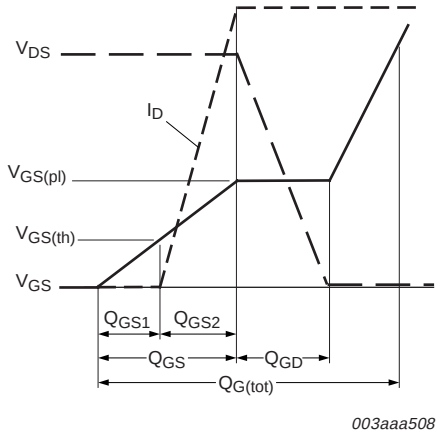
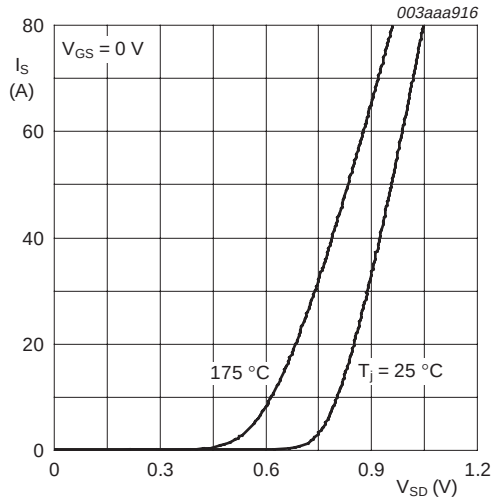
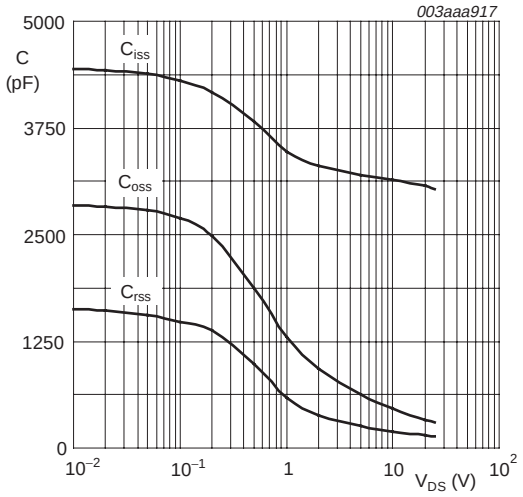


Fig 12. Gate charge waveform definitions



T_j = 25 °C and 175 °C; V_{GS} = 0 V

Fig 13. Source current as a function of source-drain voltage; typical values

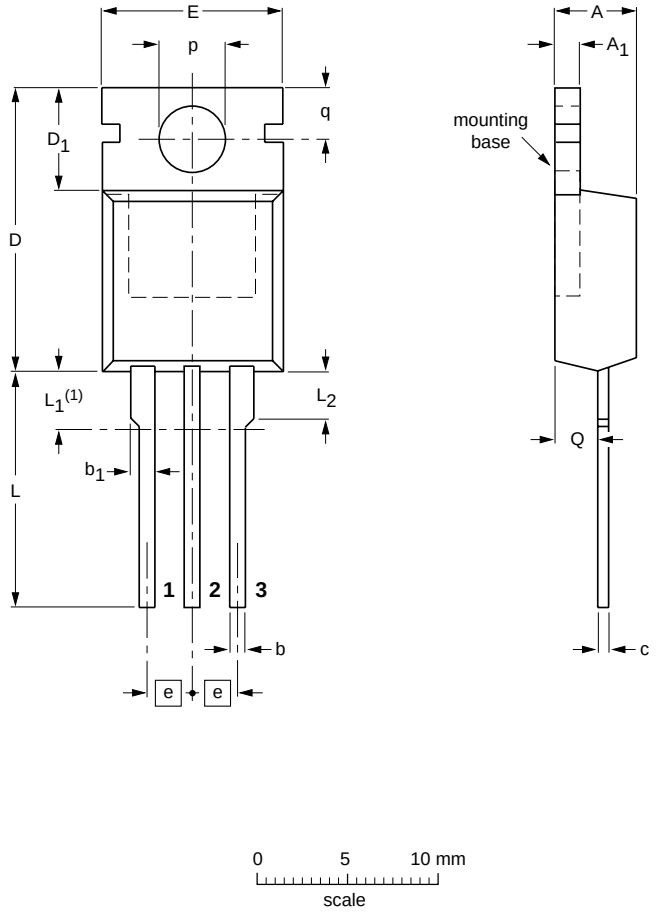


V_{GS} = 0 V; f = 1 MHz

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D	D_1	E	e	L	L_1	L_2 max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.45 1.00	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~05-01-31~~ 05-03-22

Fig 15. Package outline SOT78 (3-lead TO-220AB)

8. Revision history

Table 6: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PHP79NQ08LT_1	20050721	Product data sheet	-	9397 750 15181	-

9. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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14. Contents

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